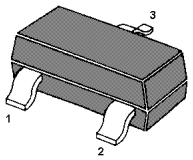
BF821

PNP Silicon High Voltage Transistors

for high voltage switching and amplifier applications.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	300	V
Collector Emitter Voltage	$-V_{CEO}$	300	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	50	mA
Peak Collector Current	$-I_{CM}$	100	mA
Peak Base Current	$-I_{BM}$	50	mA
Total Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE}$ = 20 V, $-I_C$ = 25 mA	h_{FE}	50	-	-
Collector Base Cutoff Current at $-V_{CB}$ = 200 V	$-I_{CBO}$	-	10	nA
Emitter Base Cutoff Current at $-V_{EB}$ = 5 V	$-I_{EBO}$	-	50	nA
Collector Base Breakdown Voltage at $-I_C$ = 100 µA	$-V_{(BR)CBO}$	300	-	V
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	$-V_{(BR)CEO}$	300	-	V
Emitter Base Breakdown Voltage at $-I_E$ = 100 µA	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 30 mA, $-I_B$ = 5 mA	$-V_{CE(sat)}$	-	0.8	V
Current Gain Bandwidth Product at $-V_{CE}$= 10 V, $-I_C$ = 10 mA, f = 100 MHz	f_T	60	-	MHz
Collector Output Capacitance at $-V_{CB}$ = 20 V, f = 1 MHz	C_{ob}	-	6	pF